200V N-Channel Trench Power MOSFET

General Description

The SJ02N170 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a wide variety of applications.

Features

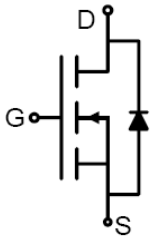
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handing capability
- Lead free product is acquired

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	200	V
$R_{DS(ON)\_TYP}$	20	mΩ
I_D	65	A
Q_G	134	nC



Schematic Diagram

TO-220 top view

RoHS

Device/Ordering Code	Marking	Package	Reel Size	Tape width	Quantity
SJ02N170	SJ02N170	TO-220	\	\	\

Table 1. Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	200	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±20	V
I_D	Drain Current-Continuous(T_C=25℃)	65	A
	Drain Current-Continuous(T_C=100℃)	41	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	260	A
P_D	Maximum Power Dissipation(T_C=25℃)	272	W
	Maximum Power Dissipation(T_C=100℃)	109	W
E_{AS}	Avalanche energy (Note 2)	1190	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.46	℃/W

Table 3. Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	200			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=150V, V_{GS}=0V T_J=25℃			1	μA
		V_{DS}=150V, V_{GS}=0V T_J=125℃			100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	3		5	V
g_{FS}	Forward Transconductance	V_{DS}=10V, I_D=20A		73		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=40A T_J=25℃		20	25.5	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=50V,V_{GS}=0V, f=1.0MHz		8826		pF
C_{oss}	Output Capacitance			532		pF
C_{rss}	Reverse Transfer Capacitance			148		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		1.2		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=10V, V_{DS}=50V, R_L=1.25Ω, R_{GEN}=3Ω		36.3		nS
t_r	Turn-on Rise Time			9.2		nS
$t_{d(off)}$	Turn-Off Delay Time			64		nS
t_f	Turn-Off Fall Time			6.3		nS
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=50V, I_D=40A		134		nC
Q_{gs}	Gate-Source Charge			49.6		nC
Q_{gd}	Gate-Drain Charge			39.6		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				65	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=20A			1.2	V
t_{rr}	Reverse Recovery Time	I_F=40A, dI/dt=100A/μs		102		ns
Q_{rr}	Reverse Recovery Charge	I_F=40A, dI/dt=100A/μs		550.3		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=40V,V_G=10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

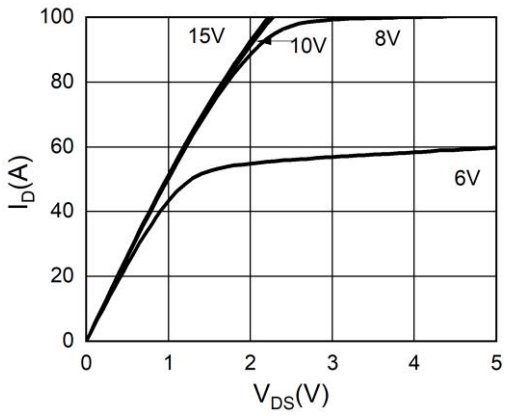


Figure 2. Transfer Characteristics

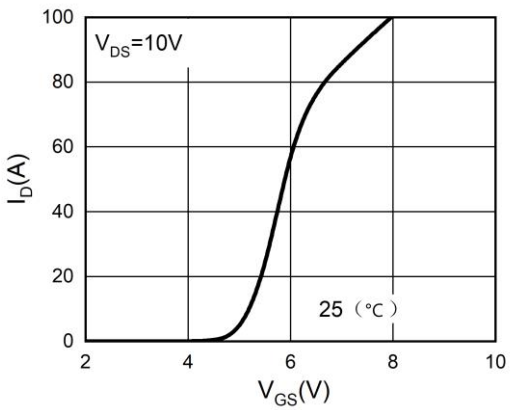


Figure 3. Power Dissipation

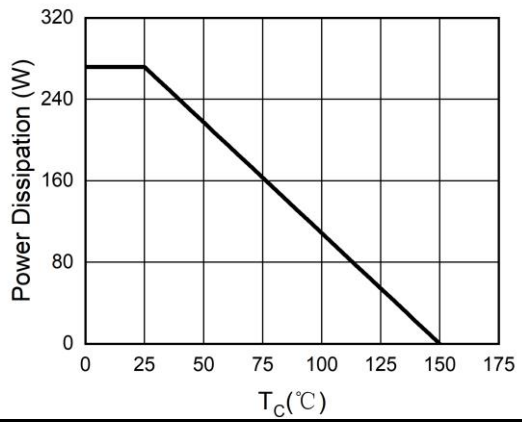


Figure 4. Drain Current

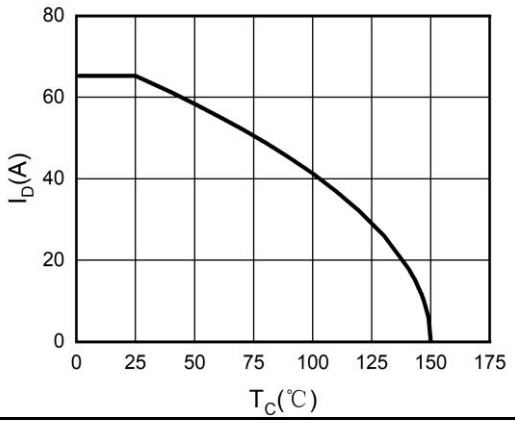


Figure 5. BV_{DSS} vs Junction Temperature

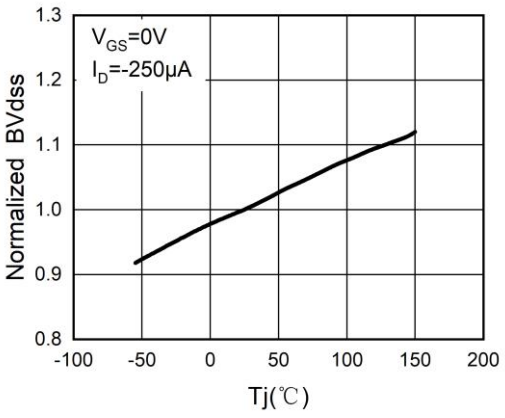
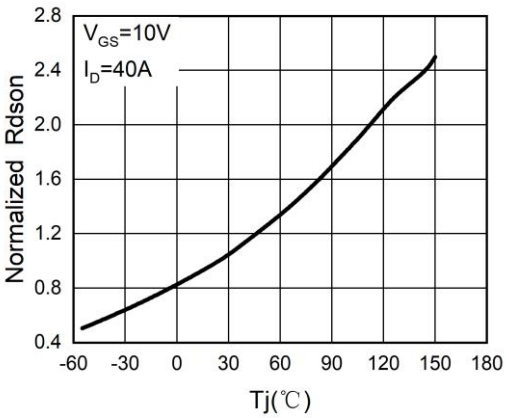


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

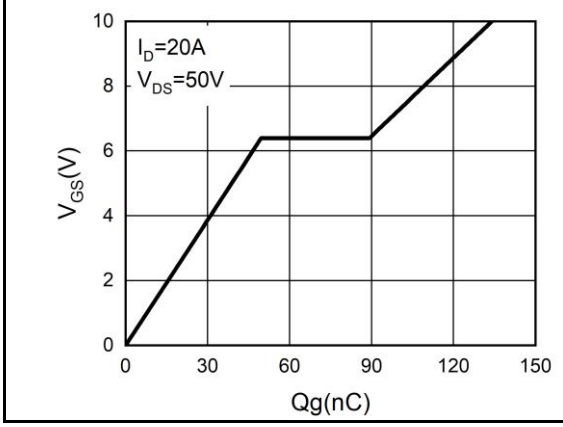


Figure 8. Capacitance

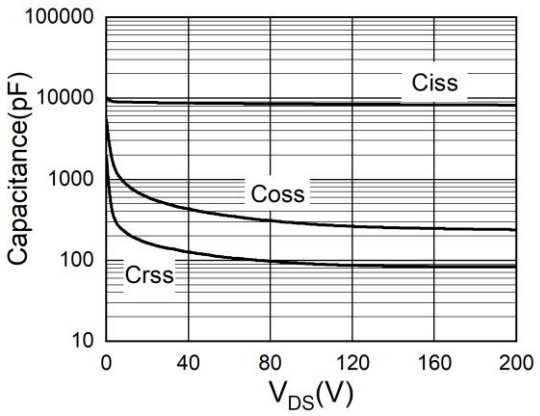


Figure 9. Body-Diode Characteristics

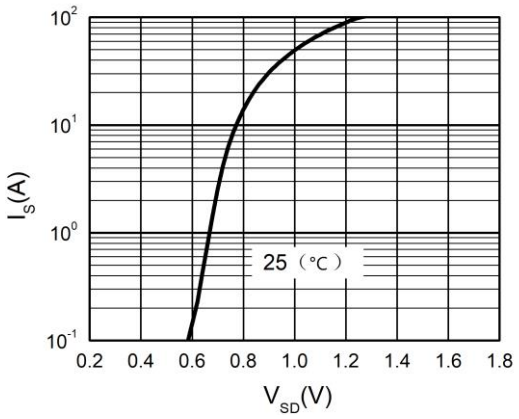
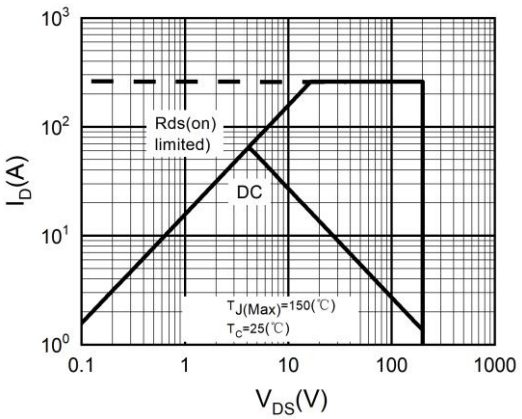
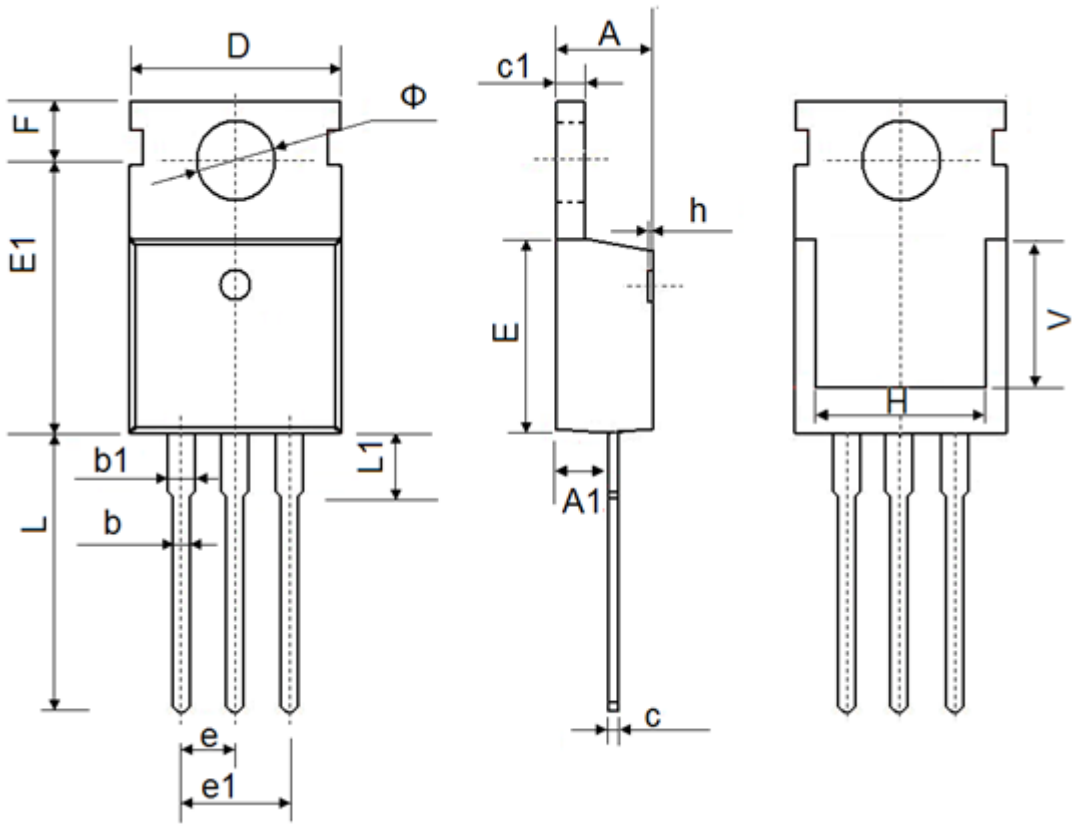


Figure 10. Maximum Safe Operating Area



TO-220 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max
A	4.300	4.700	0.169	0.185
A1	2.200	2.600	0.087	0.102
b	0.700	0.950	0.028	0.037
b1	1.170	1.410	0.046	0.056
c	0.450	0.650	0.018	0.026
c1	1.200	1.400	0.047	0.055
D	9.600	10.400	0.378	0.409
E	8.8500	9.750	0.348	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.750	14.300	0.502	0.563
L1	2.850	3.950	0.112	0.156
V	7.500 REF.		0.295 REF.	
Φ	3.400	4.000	0.134	0.157

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